

## **HAT2038R, HAT2038RJ**

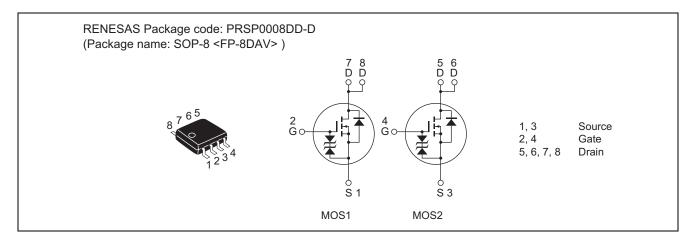
# Silicon N Channel Power MOS FET High Speed Power Switching

REJ03G1167-0600 Rev.6.00 Aug 25, 2009

### **Features**

- For Automotive Application (at Type Code "J")
- Low on-resistance
- Capable of 4 V gate drive
- High density mounting

### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item		Symbol	Value	Unit
Drain to source voltage		$V_{DSS}$	60	V
Gate to source voltage		$V_{GSS}$	±20	V
Drain current		$I_D$	5	Α
Drain peak current		I <sub>D (pulse)</sub> Note 1	40	Α
Body-drain diode reverse drain current		I <sub>DR</sub>	5	Α
Avalanche current	HAT2038R	I <sub>AP</sub> Note 4	_	_
	HAT2038RJ		5	Α
Avalanche energy	HAT2038R	E <sub>AR</sub> Note 4	_	_
	HAT2038RJ		2.14	mJ
Channel dissipation		Pch Note 2	2	W
Channel dissipation		Pch Note 3	3	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. 1 Drive operation: When using the glass epoxy board (FR4  $40 \times 40 \times 1.6$  mm), PW  $\leq 10$  s
- 3. 2 Drive operation: When using the glass epoxy board (FR4  $40 \times 40 \times 1.6$  mm), PW  $\leq 10$  s
- 4. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$

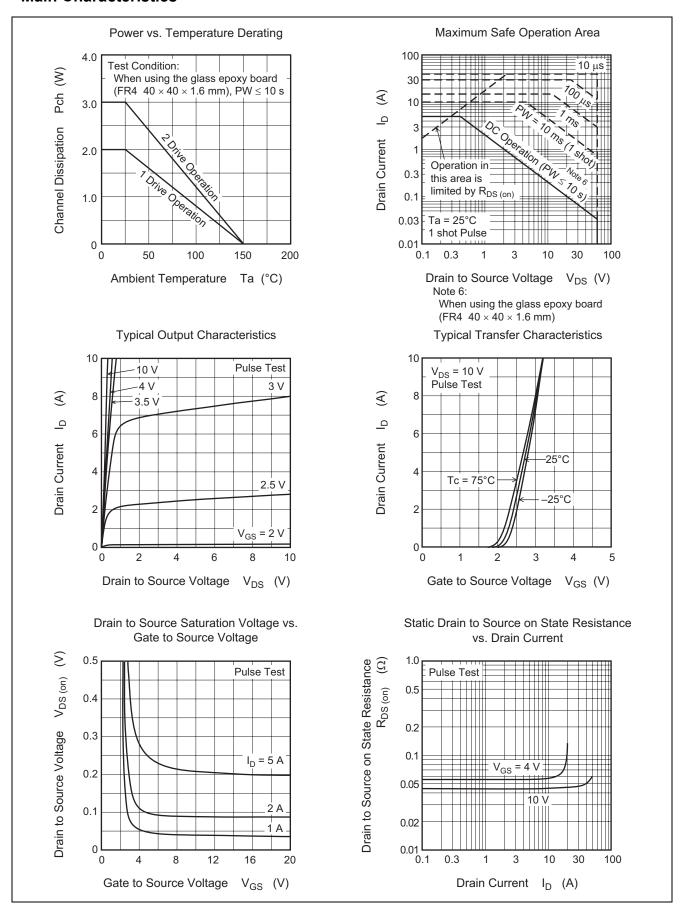
### **Electrical Characteristics**

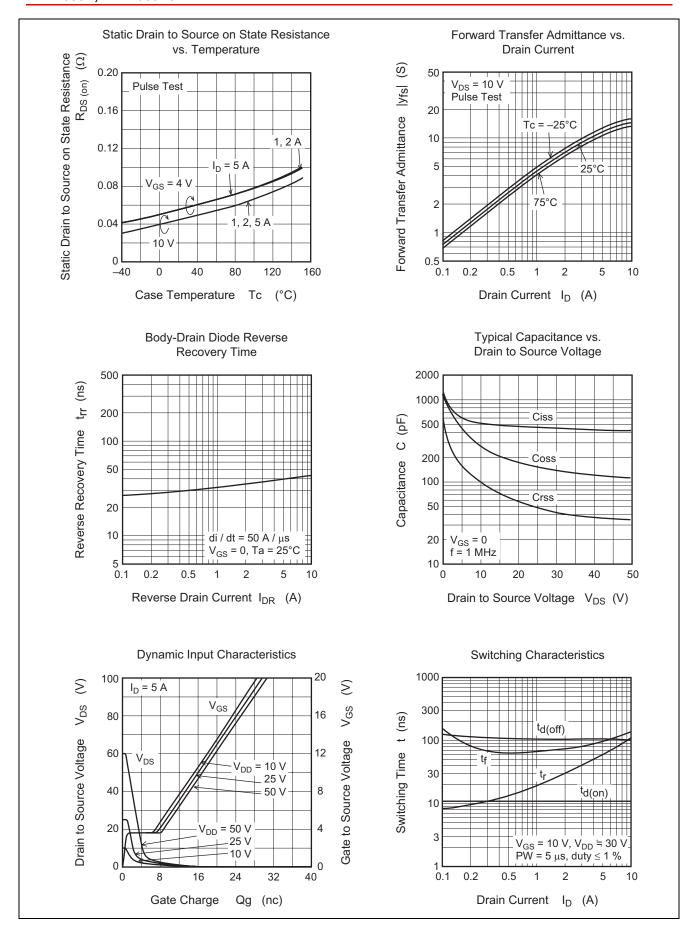
 $(Ta = 25^{\circ}C)$ 

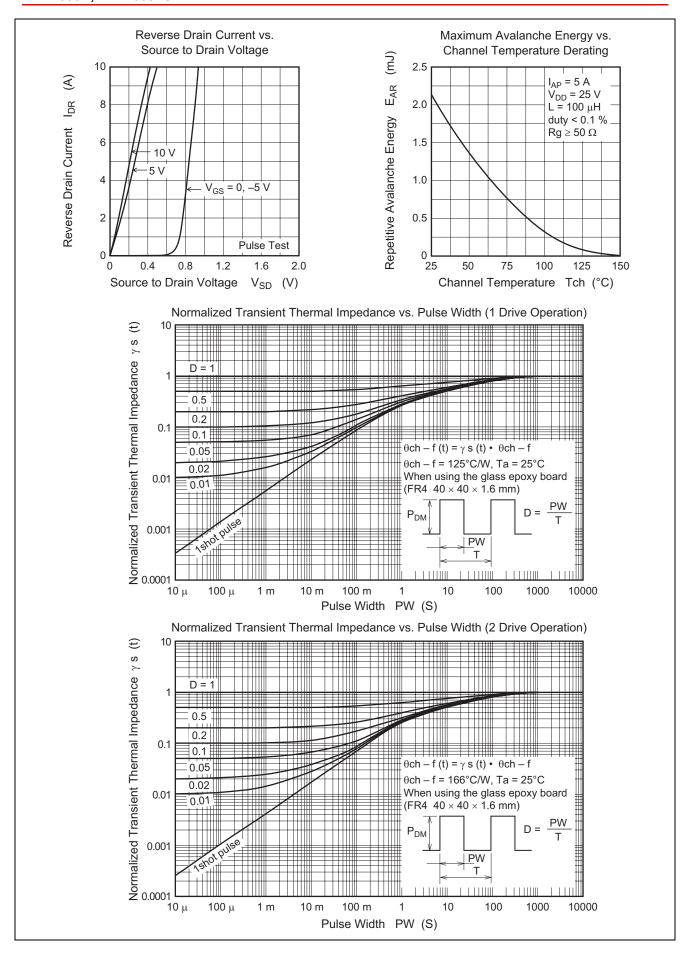
Item		Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage		V <sub>(BR) DSS</sub>	60	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage		V <sub>(BR) GSS</sub>	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current		I <sub>GSS</sub>	_	_	±10	μА	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain	HAT2038R	I <sub>DSS</sub>	_	_	1	μА	$V_{DS} = 60 \text{ V}, V_{GS} = 0$
current	HAT2038RJ	I <sub>DSS</sub>	_	_	0.1	μА	
Zero gate voltage drain	HAT2038R	I <sub>DSS</sub>	_	_	_	μА	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0
current	HAT2038RJ	I <sub>DSS</sub>	_	_	10	μА	Ta = 125°C
Gate to source cutoff voltage		V <sub>GS (off)</sub>	1.2	_	2.2	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance		R <sub>DS (on)</sub>	_	0.043	0.058	Ω	$I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 5}}$
		R <sub>DS (on)</sub>	_	0.056	0.084	Ω	$I_D = 3 A, V_{GS} = 4 V^{\text{Note 5}}$
Forward transfer admittance		y <sub>fs</sub>	6	9	_	S	$I_D = 3 A, V_{DS} = 10 V^{Note 5}$
Input capacitance		Ciss	_	520	_	pF	V <sub>DS</sub> = 10 V
Output capacitance		Coss	_	270	_	pF	$V_{GS} = 0$
Reverse transfer capacitance		Crss	_	100		рF	f = 1 MHz
Turn-on delay time		t <sub>d (on)</sub>		11	_	ns	$V_{GS} = 10 \text{ V}, I_D = 3 \text{ A},$
Rise time		t <sub>r</sub>	_	40		ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time		t <sub>d (off)</sub>	_	110	_	ns	
Fall time		t <sub>f</sub>	_	80	_	ns	
Body-drain diode forward voltage		$V_{DF}$	_	0.84	1.1	V	$I_F = 5 \text{ A}, V_{GS} = 0^{\text{Note } 5}$
Body-drain diode reverse recovery time		t <sub>rr</sub>	_	40	_	ns	I <sub>F</sub> = 5 A, V <sub>GS</sub> = 0
							di <sub>F</sub> /dt = 50 A/μs

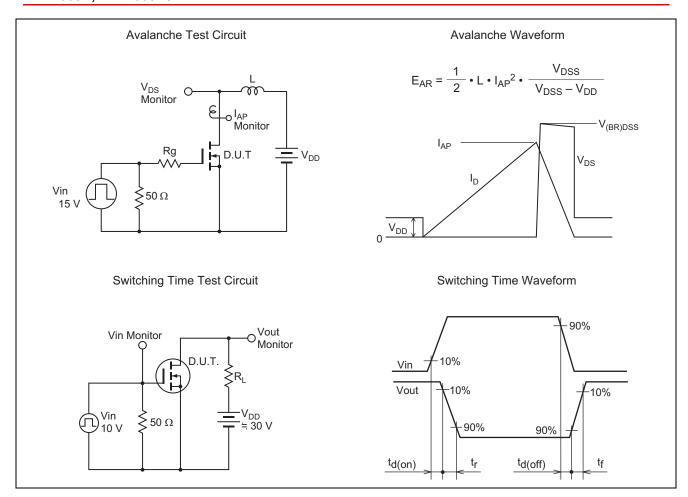
Note: 5. Pulse test

### **Main Characteristics**

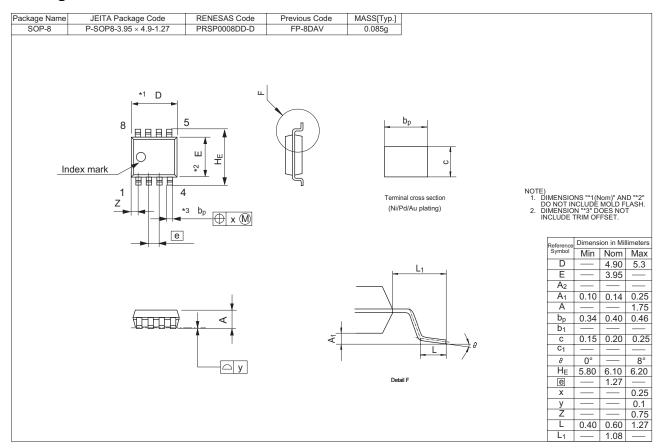








### **Package Dimensions**



### **Ordering Information**

Part Name	Quantity	Shipping Container
HAT2038R-EL-E	2500 pcs	Taping
HAT2038RJ-EL-E	2500 pcs	Taping

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